

November 2013

N-Channel QFET[®] MOSFET 600 V, 2.8 A, 2.5 Ω

Features

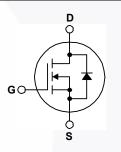
- 2.8 A, 600 V, $R_{DS(on)}$ = 2.5 Ω (Max.) @ V_{GS} = 10 V, I_D = 1.4 A
- Low Gate Charge (Typ. 15 nC)
- Low Crss (Typ. 6.5 pF)
- 100% Avalanche Tested
- RoHS compliant

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.







Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

| Symbol | Parameter | | FQD5N60CTM / FQU5N60CTU | Unit |
|-----------------------------------|---|----------|-------------------------|------|
| V _{DSS} | Drain-Source Voltage | | 600 | V |
| I _D | Drain Current - Continuous ($T_c = 25^{\circ}C$) | | 2.8 | А |
| | - Continuous (T _C = 100°C) | | 1.8 | А |
| I _{DM} | Drain Current - Pulsed | (Note 1) | 11.2 | А |
| V _{GSS} | Gate-Source Voltage | | ± 30 | V |
| E _{AS} | Single Pulsed Avalanche Energy | (Note 2) | 210 | mJ |
| I _{AR} | Avalanche Current (Note | | 2.8 | А |
| E _{AR} | Repetitive Avalanche Energy (Not | | 4.9 | mJ |
| dv/dt | Peak Diode Recovery dv/dt (Note 3) | | 4.5 | V/ns |
| | Power Dissipation (T _A = 25°C)* | | 2.5 | W |
| PD | Power Dissipation ($T_C = 25^{\circ}C$) | | 49 | W |
| | - Derate above 25°C | | 0.39 | W/°C |
| T _J , T _{STG} | Operating and Storage Temperature Range | | -55 to +150 | °C |
| TL | Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds | 300 | °C | |

Thermal Characteristics

| Symbol | Parameter | FQD5N60CTM / FQU5N60CTU | Unit |
|-----------------------|--|----------------------------|------|
| $R_{\theta JC}$ | Thermal Resistance, Junction-to-Case, Max. | 2.56 | |
| P | Thermal Resistance, Junction-to-Ambient (minimum pad of 2 oz copper), Max. | 110 | °C/W |
| $R_{	extsf{	heta}JA}$ | Thermal Resistance, Junction-to-Ambient (* 1 in ² pad of 2 oz copper), Max. | 50 | |

| Device | Marking | Device | Package | Reel Size | Таре | Width | Qua | antity |
|---------------------------------------|----------------------------|--|---|--------------------|-------|-------|------------|--------|
| FQD! | FQD5N60C FQD5N60CTM | | D-PAK 330 mm | | 16 mm | | 2500 units | |
| FQU5N60C FQU5N60CTU | | I-PAK | I-PAK Tube | | N/A | | 70 units | |
| Electri | cal Char | racteristics T _C = 25° | °C unless otherwise | noted. | | | | |
| Symbol | | Parameter | Test C | conditions | Min | Тур | Max | Unit |
| | aracteristi | cs | | | | | | |
| BV _{DSS} | Drain-Sour | rce Breakdown Voltage | $V_{GS} = 0 V, I_D = 2$ | 250 μΑ | 600 | | | V |
| ΔBV_{DSS} / ΔT_{J} | Breakdowr Coefficient | n Voltage Temperature | I _D = 250 μA, Ref | | | 0.6 | | V/°C |
| 1 | Zoro Coto | Valtage Drain Current | V_{DS} = 600 V, V_{GS} | - | | | 1 | μA |
| IDSS | Zero Gale | Voltage Drain Current | V _{DS} = 480 V, T _C | | | | 10 | μA |
| I _{GSSF} | Gate-Body | / Leakage Current, Forward | V_{GS} = 30 V, V_{DS} | = 0 V | | | 100 | nA |
| I _{GSSR} | Gate-Body | / Leakage Current, Reverse | V_{GS} = -30 V, V_{DS} | ₃ = 0 V | | | -100 | nA |
| | aracteristi | cs | | | | | | |
| V _{GS(th)} | Gate Three | shold Voltage | $V_{DS} = V_{GS}, I_D = 2$ | 250 μΑ | 2.0 | | 4.0 | V |
| R _{DS(on)} | Static Drair On-Resista | | V _{GS} = 10 V, I _D = | | | 2.0 | 2.5 | Ω |
| 9 _{FS} | Forward Tr | ransconductance | V_{DS} = 40 V, I_{D} = | 1.4 A | | 4.7 | | S |
| Dynam | ic Charac | teristics | | | | | | |
| C _{iss} | Input Capa | citance | V _{DS} = 25 V, V _{GS} | = 0 V, | | 515 | 670 | pF |
| C _{oss} | Output Cap | | f = 1.0 MHz | | | 55 | 72 | pF |
| C _{rss} | Reverse Tr | ransfer Capacitance | | | | 6.5 | 8.5 | pF |
| Switchi | ing Chara | cteristics | | | | | | |
| t _{d(on)} | Turn-On De | elay Time | V _{DD} = 300 V, I _D = | = 4.5A. | | 10 | 30 | ns |
| t _r | Turn-On Ri | ise Time | $R_{\rm G} = 25 \Omega$ | 1.0, | | 42 | 90 | ns |
| t _{d(off)} | Turn-Off De | elay Time | | | | 38 | 85 | ns |
| t _f | Turn-Off Fa | | | (Note 4) | | 46 | 100 | ns |
| Qg | Total Gate | | V _{DS} = 480 V, I _D = | = 4.5A, | | 15 | 19 | nC |
| Q _{gs} | Gate-Source | - | V _{GS} = 10 V | | | 2.5 | | nC |
| Q _{gd} | Gate-Drain | ı Charge | | (Note 4) | | 6.6 | | nC |
| Droin S | | ada Charactoristica (| and Maximum E | Potingo | | | | |
| | | ode Characteristics a Continuous Drain-Source D | | - | 1 | 1 | 2.8 | |
| le | | COMMUNICAS DIAIN-SOURCE P | looe Folwalo Culle | (1) | | | | A |

| ا _S | Maximum Continuous Drain-Source Diode Forward Current | | | | 2.8 | A |
|-----------------|---|--|---|-----|------|----|
| I _{SM} | Maximum Pulsed Drain-Source Diode Forward Current | | | | 11.2 | А |
| V _{SD} | Drain-Source Diode Forward Voltage | V _{GS} = 0 V, I _S = 2.8 A | | - | 1.4 | V |
| t _{rr} | Reverse Recovery Time | V _{GS} = 0 V, I _S = 4.5 A, | | 300 | | ns |
| Q _{rr} | Reverse Recovery Charge $dI_F / dt = 100 A/\mu s$ | | 1 | 2.2 | | μC |

NOTES:

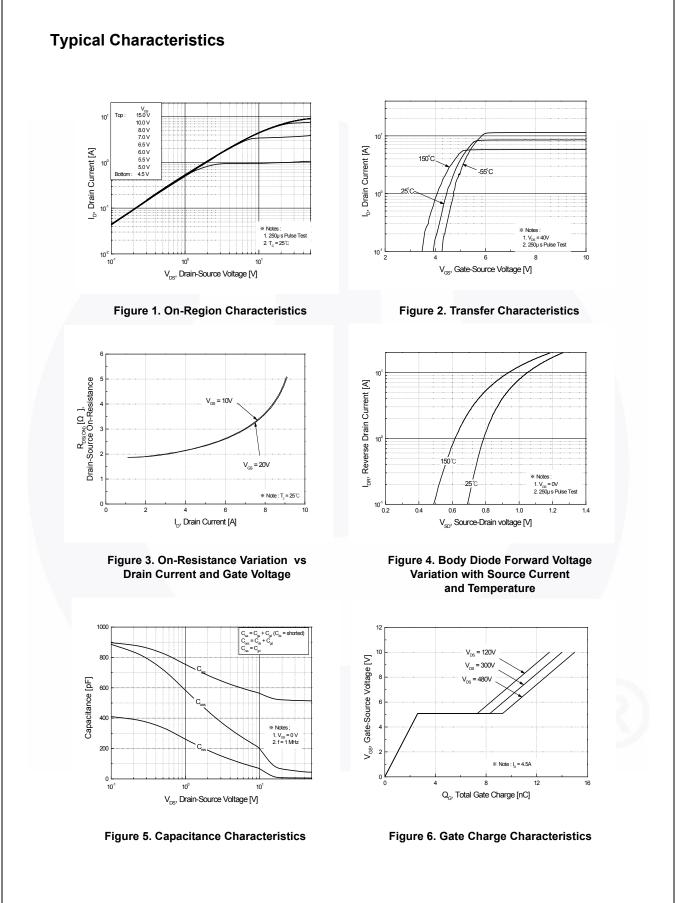
1. Repetitive Rating : Pulse width limited by maximum junction temperature.

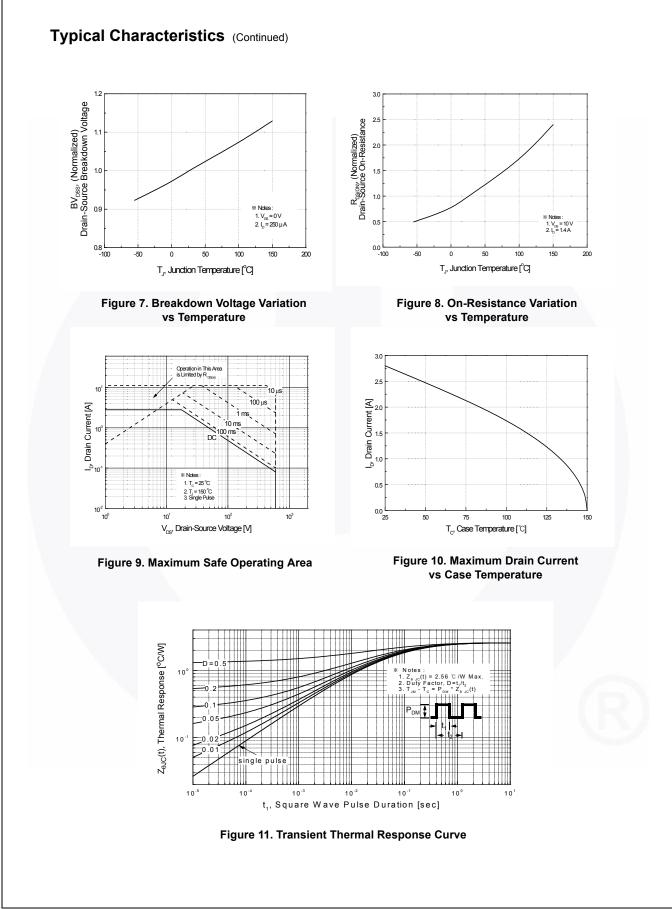
Package Marking and Ordering Information

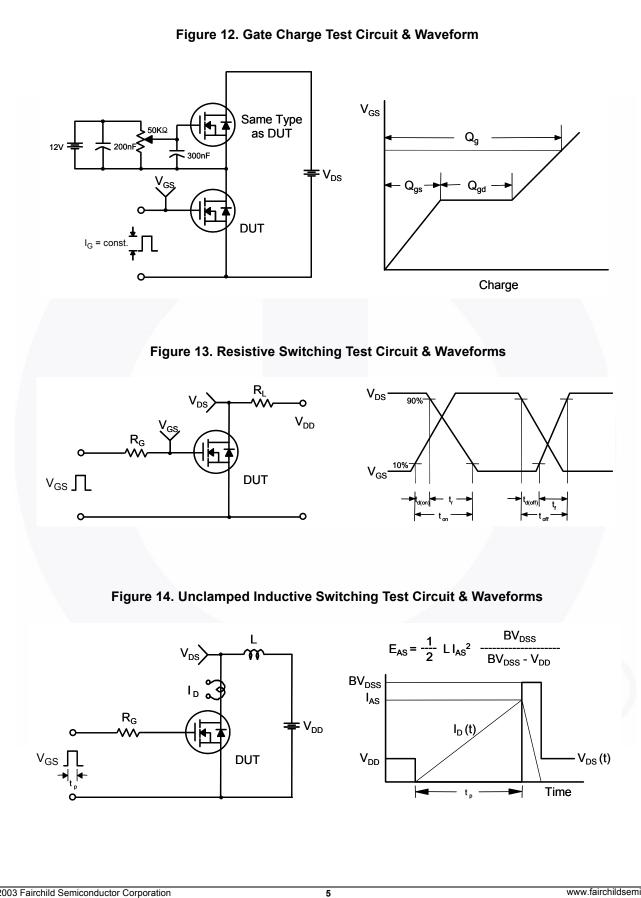
2. L = 18.9mH, I_{AS} = 4.5 A, V_{DD} = 50V, R_G = 25 $\Omega,$ starting $\mbox{ T}_{J}$ = 25°C.

3. I_{SD} \leq 4.5A, di/dt \leq 200A/µs, V_{DD} \leq BV_{DSS,} starting ~T_J = 25°C.

4. Essentially independent of operating temperature.







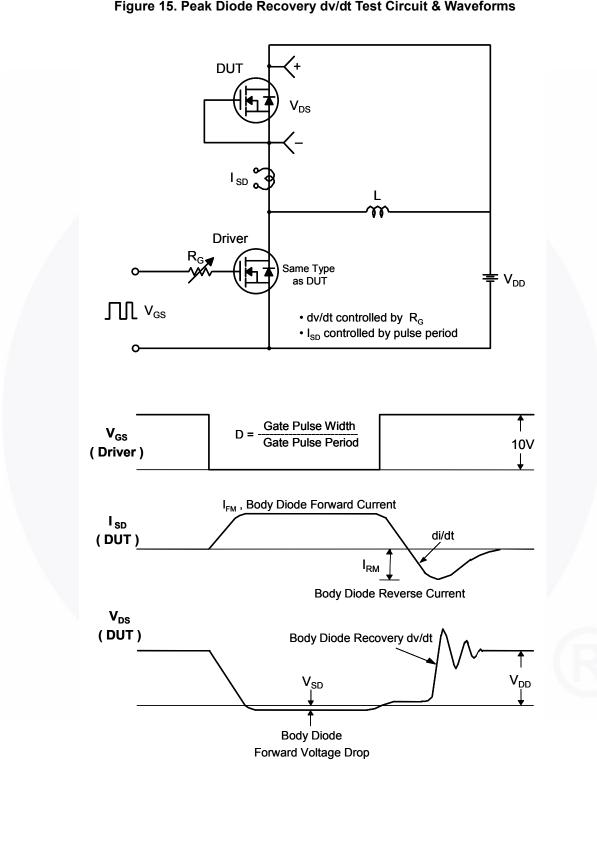
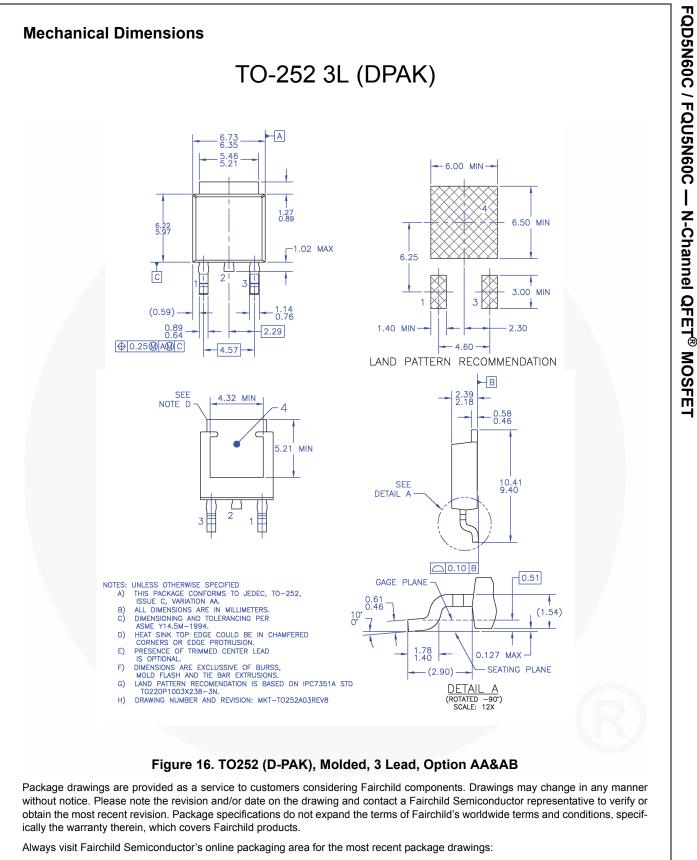
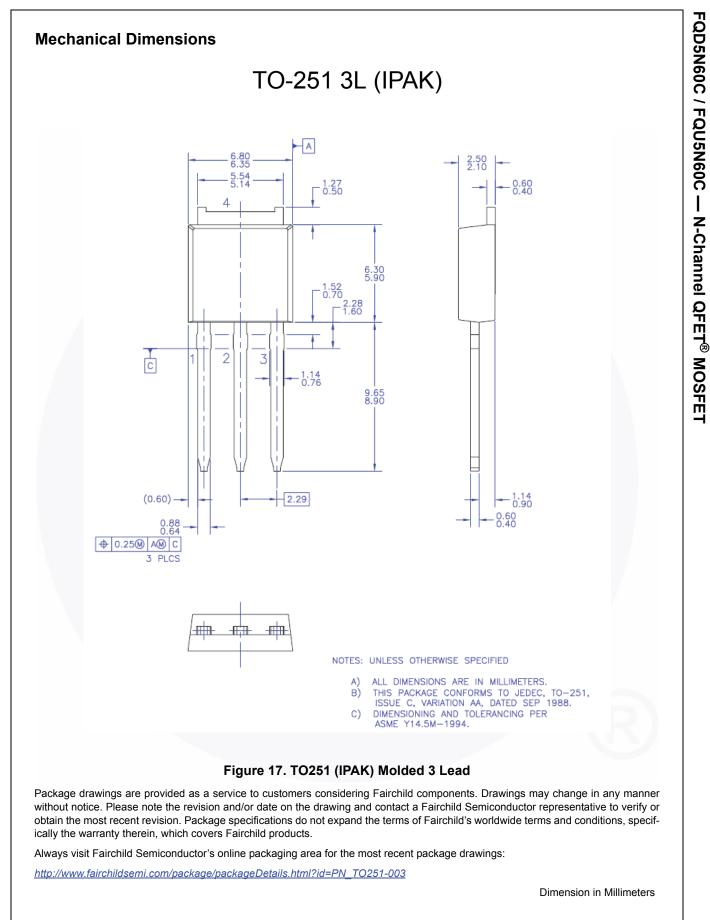


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms



http://www.fairchildsemi.com/package/packageDetails.html?id=PN_TT252-003

Dimension in Millimeters





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